



DESCRIPTION

AM1465H is available in a TO-252 package.

FEATURES

- Available in a TO-252 package.

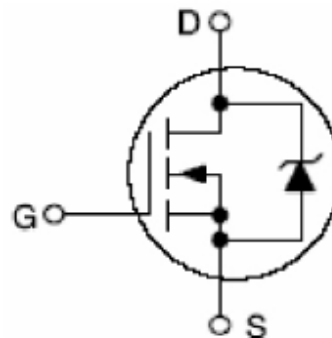
ORDERING INFORMATION

| Package Type | Part Number | |
|--------------------------------|---|------------|
| TO-252 SPQ: 2,500pcs/Reel | D | AM1465HDR |
| | | AM1465HDVR |
| Note | V: Halogen free Package R: Tape & Reel | |
| AiT provides all RoHS products | | |

APPLICATION

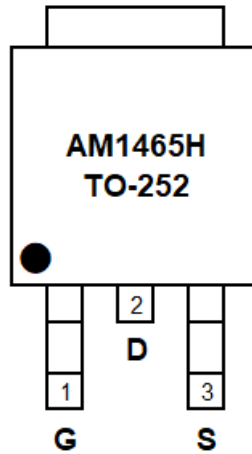
- Advanced charge balance Technology

PIN DESCRIPTION





PIN DESCRIPTION



Top View

| Pin # | Symbol | Function |
|-------|--------|----------|
| 1 | G | Gate |
| 2 | D | Drain |
| 3 | S | Source |



ABSOLUTE MAXIMUM RATINGS

| | | |
|--|--------|--------------|
| V _{DS} , Drain-Source Voltage | | 650V |
| I _D , Drain Current-Continuous | @25°C | 14A |
| | @100°C | 8.4A |
| I _{DM} , Pulsed Drain Current ^{NOTE1} | | 56A |
| V _{GS} , Gate-Source Voltage | | ±30V |
| T _J , T _{STG} , Operating Junction & Storage Temperature | | -55°C~+150°C |
| T _L , Lead Temperature (1/16" from case for 10sec.) | | 300°C |

Stress beyond above listed "Absolute Maximum Ratings" may lead permanent damage to the device. These are stress ratings only and operations of the device at these or any other conditions beyond those indicated in the operational sections of the specifications are not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

ELECTRICAL CHARACTERISTICS

| Parameter | Symbol | Conditions | Min | Typ. | Max | Units |
|--|----------------------|--|-----|------|------|-------|
| Static | | | | | | |
| Drain-Source Breakdown Voltage | V _{(BR)DSS} | V _{GS} =0V, I _D =250μA | 650 | - | - | V |
| Gate Threshold Voltage | V _{GS(th)} | V _{DS} =V _{GS} , I _D =250μA | 2 | 3 | 4 | V |
| Gate Leakage Current | I _{GSS} | V _{DS} =0V, V _{GS} =±30V | - | - | ±100 | nA |
| Zero Gate Voltage Drain Current | I _{DSS} | V _{DS} =650V, V _{GS} =0V | - | - | 1 | μA |
| | | V _{DS} =650V, V _{GS} =0V | - | - | 10 | |
| | | T _J =150°C | - | - | 10 | |
| Drain-source On-Resistance ^{NOTE2} | R _{DS(ON)} | V _{GS} =10V, I _D =6.9A | - | 210 | 250 | mΩ |
| Source-Drain Diode Ratings and Characteristics (T_C = 25°C) | | | | | | |
| Continuous Current | I _S | | - | - | 14 | A |
| Forward Voltage | V _{SD} | I _S =5.5A, V _{GS} =0V | - | 0.88 | 1.1 | V |

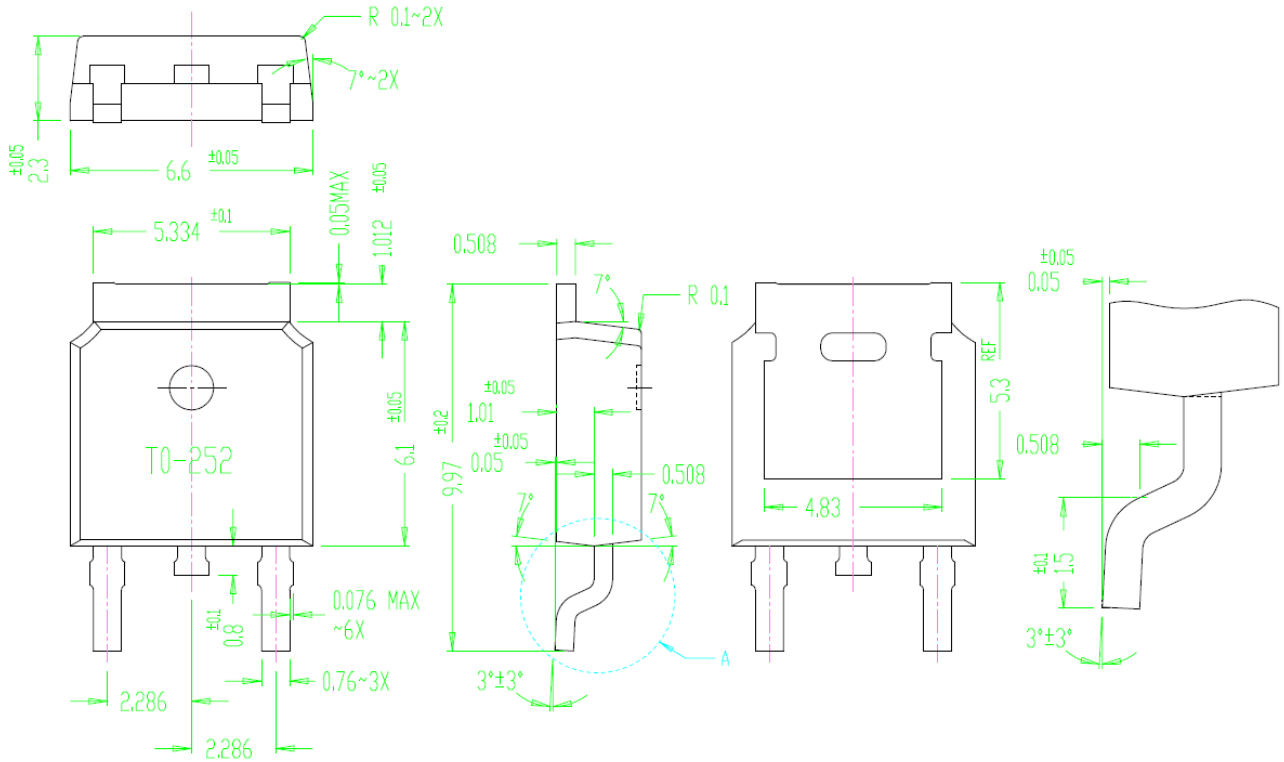
NOTE1: Pulse width limited by maximum junction temperature.

NOTE2: R_{DS(ON)} based on the following conditions. Only for reference. Package type: TO-252 Source area bonding wire: 1*15mil AL.



PACKAGE INFORMATION

Dimension in TO-252 (Unit: mm)





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